

isc Silicon NPN Power Transistor

BU2525AF

DESCRIPTION

- Collector-Emitter Sustaining Voltage-
: $V_{CEO(SUS)} = 800V$ (Min)
- High Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

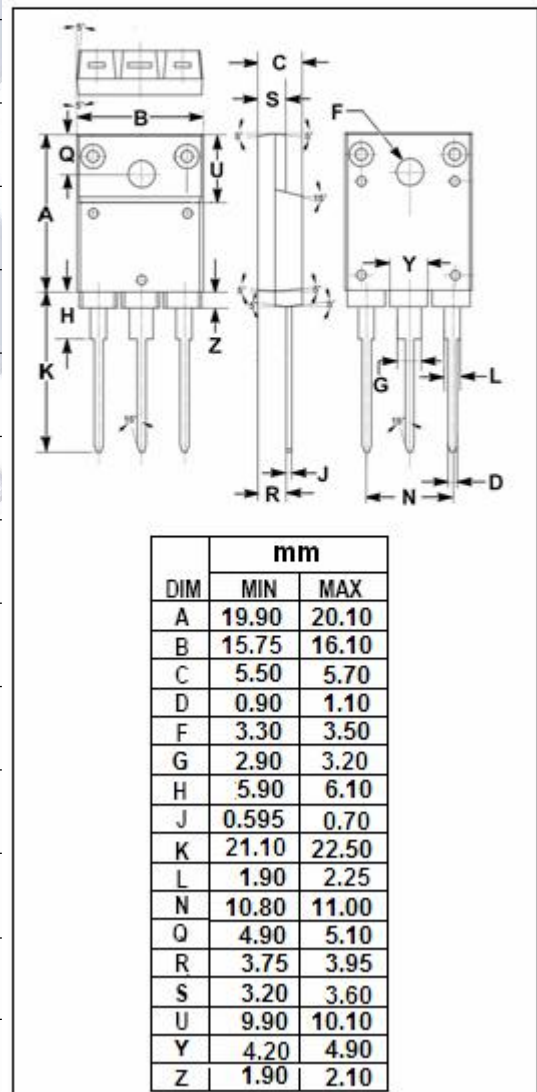
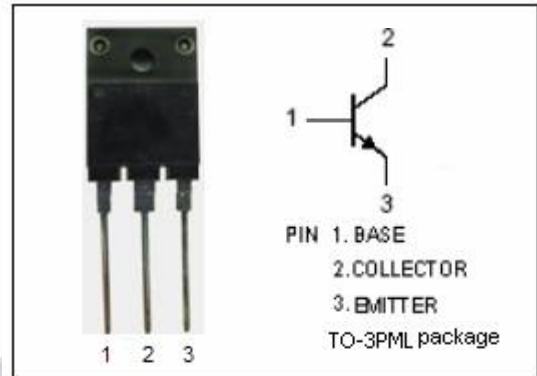
- Designed for use in horizontal deflection circuits of high resolution monitors.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CESM}	Collector- Emitter Voltage Peak value	1500	V
V_{CEO}	Collector-Emitter Voltage	800	V
V_{EBO}	Emitter-Base Voltage	7.5	V
I_C	Collector Current- Continuous	12	A
I_{CM}	Collector Current-Peak	30	A
I_B	Base Current- Continuous	8	A
P_C	Collector Power Dissipation @ $T_C=25^\circ C$	80	W
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-65~150	$^\circ C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R_{thj-c}	Thermal Resistance, Junction to Case	1.56	$^\circ C/W$



isc Silicon NPN Power Transistor**BU2525AF****ELECTRICAL CHARACTERISTICS** $T_c=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=50\text{mA}; I_B=0$	800			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=1\text{mA}; I_C=0$	7.5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=8\text{A}; I_B=1.6\text{A}$			5.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=8\text{A}; I_B=1.6\text{A}$			1.1	V
I_{CES}	Collector Cutoff Current	$V_{CE}=1500\text{V}; V_{BE}=0$ $V_{CE}=1500\text{V}; V_{BE}=0; T_c=125^\circ\text{C}$			1.0 2.0	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=7.5\text{V}; I_C=0$			1.0	mA
h_{FE-1}	DC Current Gain	$I_C=0.1\text{A}; V_{CE}=5\text{V}$		13		
h_{FE-2}	DC Current Gain	$I_C=8\text{A}; V_{CE}=5\text{V}$	5	7	9.5	
C_{OB}	Output Capacitance	$I_E=0; V_{CB}=10\text{V}; f_{test}=1\text{MHz}$		145		pF